

N-Channel Super Junction Power MOSFET

General Description

The series of devices use advanced trench gate super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

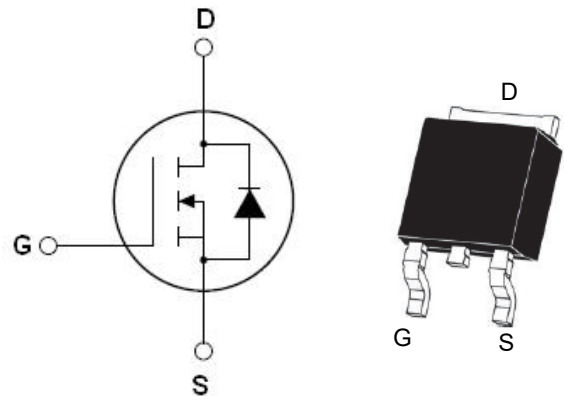
$V_{DS\ min@T_{jmax}}$	985	V
$R_{DS(ON)TYP.}$	720	mΩ
I_D	7	A
Q_g	18	nC

Features

- Optimized body diode reverse recovery performance
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- Ro HS compliant
- Halogen-free

Application

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)
- LLC Half-bridge



Schematic diagram

TO-252

Package Marking And Ordering Information

Device Marking	Device	Device Package	Packaging Code	Reel Size	Quantity(PCS)
7N900	RM7N900LD	TO-252	-W	13inch	2500

Table 1. Absolute Maximum Ratings ($T_J=25^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS}=0V$)	V_{DS}	900	V
Gate-Source Voltage ($V_{DS}=0V$), AC ($f>1\text{ Hz}$)	V_{GS}	± 30	V
Gate-Source Voltage ($V_{DS}=0V$), DC	V_{GS}	± 20	V
Continuous Drain Current at $T_c=25^{\circ}\text{C}$	$I_{D(DC)}$	7	A
Continuous Drain Current at $T_c=100^{\circ}\text{C}$	$I_{D(DC)}$	4.9	A
Pulsed drain current (Note 1)	$I_{DM(pluse)}$	21	A
Maximum Power Dissipation($T_c=25^{\circ}\text{C}$)	P_D	98	W
Derate above 25°C		0.65	W/ $^{\circ}\text{C}$
Single pulse avalanche current (Note 2)	I_{AS}	1.0	A
Reverse diode dv/dt, $V_{DS} \leq 480\text{ V}, I_{SD} < I_D$	dv/dt	15	V/ns
Drain Source voltage slope, $V_{DS} \leq 480\text{ V}$	dv/dt	50	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55...+175	$^{\circ}\text{C}$

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Maximum)	R_{thJC}	1.53	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient (Maximum)	R_{thJA}	62	$^{\circ}\text{C}/\text{W}$

Table 3. Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250uA	900			V
Zero Gate Voltage Drain Current(Tc=25℃)	I _{DSS}	V _{DS} =900V,V _{GS} =0V			1	μA
Zero Gate Voltage Drain Current(Tc=125℃)	I _{DSS}	V _{DS} =900V,V _{GS} =0V			50	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V			±200	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250uA	3		4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =3.5A		720	800	mΩ
Dynamic Characteristics						
Gate Resistance	R _g	F=1MHZ, D-S short		5		Ω
Input Capacitance	C _{iss}	V _{DS} =50V,V _{GS} =0V, F=1MHz		810		pF
Output Capacitance	C _{oss}			46		pF
Reverse Transfer Capacitance	C _{rss}			9		pF
Total Gate Charge	Q _g	V _{DS} =600V,I _D =3.5A, V _{GS} =10V		18		nC
Gate-Source Charge	Q _{gs}			4.5		nC
Gate-Drain Charge	Q _{gd}			7.1		nC
Gate plateau voltage	V _{gp}			5.3		V
Switching times						
Turn-on Delay Time	t _{d(on)}	V _{DD} =600V,I _D =3.5A, R _G =4Ω,V _{GS} =10V		32		nS
Turn-on Rise Time	t _r			19		nS
Turn-Off Delay Time	t _{d(off)}			51		nS
Turn-Off Fall Time	t _f			14		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I _{SD}	T _C =25℃			7	A
Pulsed-Source-drain current(Body Diode)	I _{SDM}				21	A
Forward on voltage	V _{SD}	T _j =25℃,I _{SD} =7A,V _{GS} =0V		0.9	1.1	V
Reverse Recovery Time	t _{rr}	T _j =25℃,I _F =3.5A, di/dt=100A/μs		200		nS
Reverse Recovery Charge	Q _{rr}			1.45		uC
Peak reverse recovery current	I _{rrm}			14.5		A

Notes: 1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. $T_J=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, R_G=25\Omega, L=10\text{mH}$

RATING AND CHARACTERISTICS CURVES (RM7N900LD)

Figure1. Safe operating area

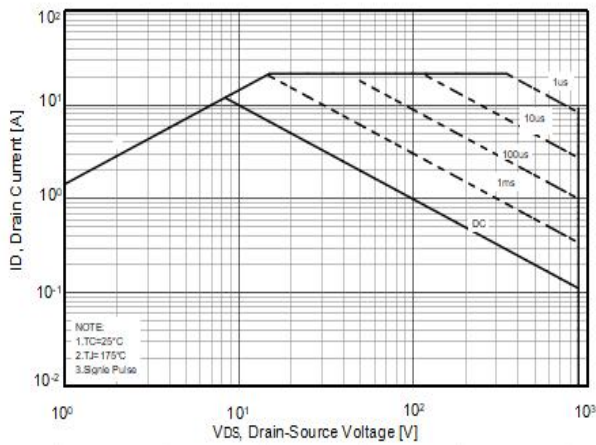


Figure2. $R_{DS(ON)}$ vs Junction Temperature

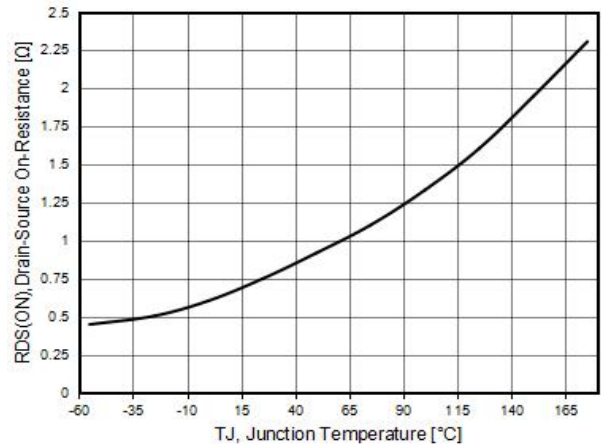


Figure3. BV_{DSS} vs Junction Temperature

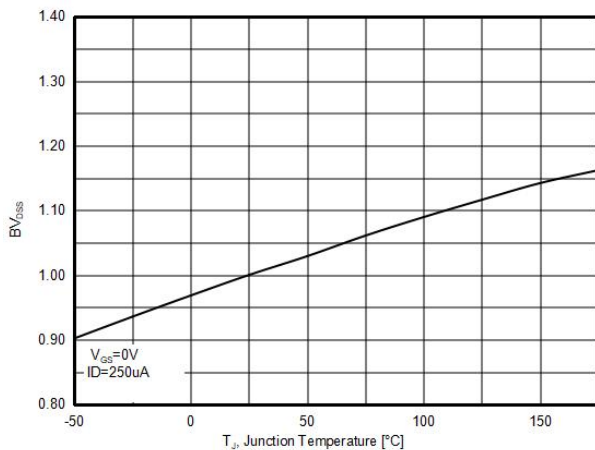
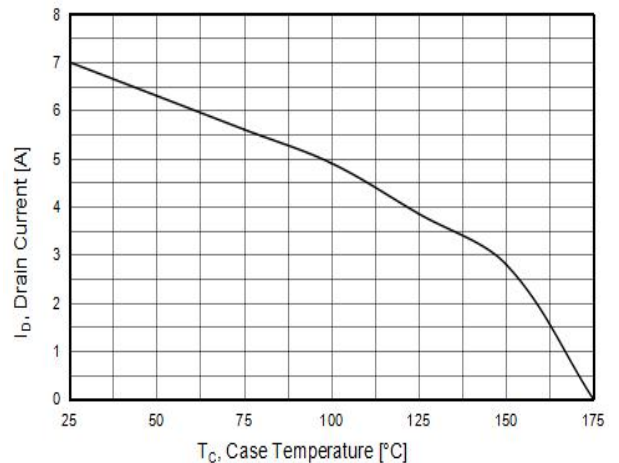
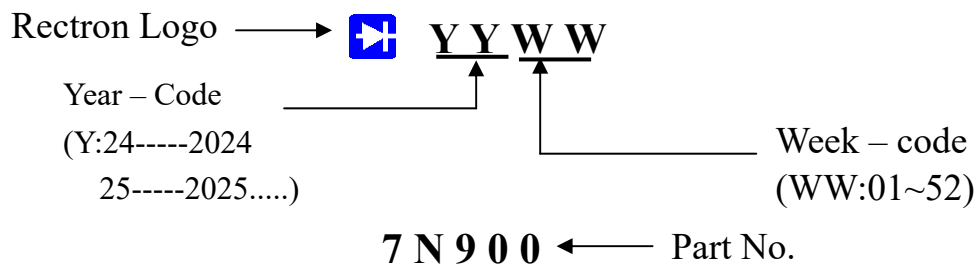


Figure4. Maximum I_D vs Junction Temperature



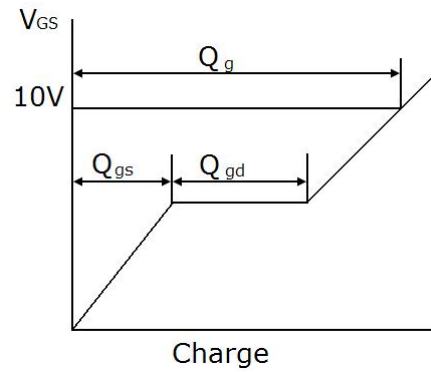
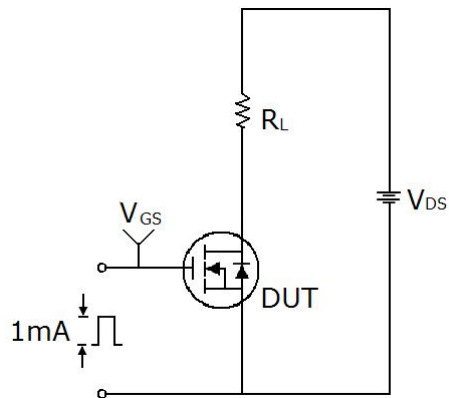
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Marking on the body

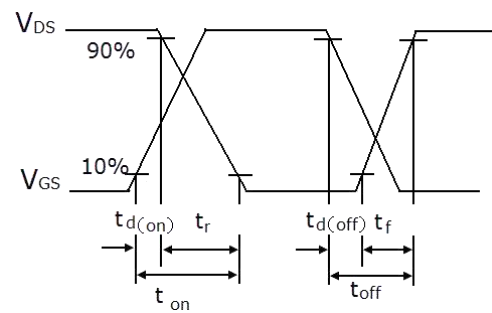
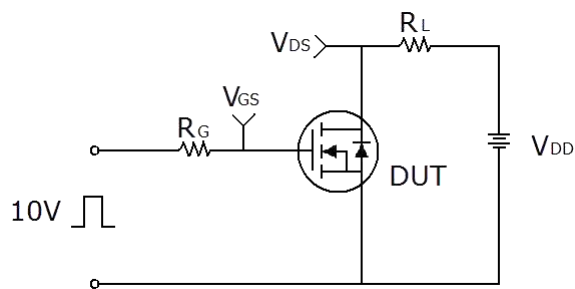


Test circuit

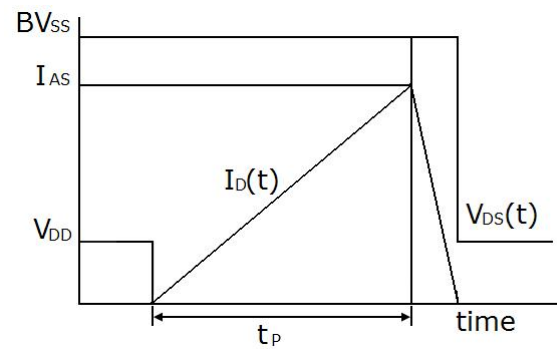
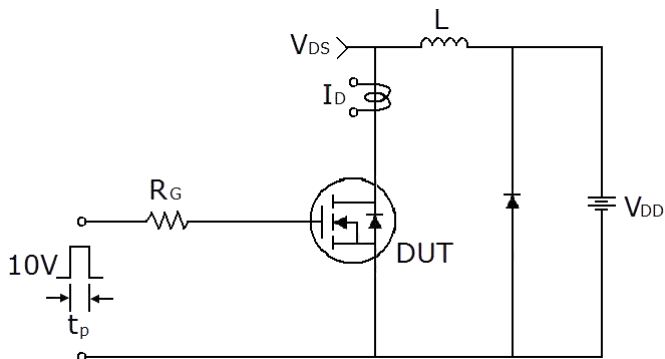
1) Gate charge test circuit & Waveform



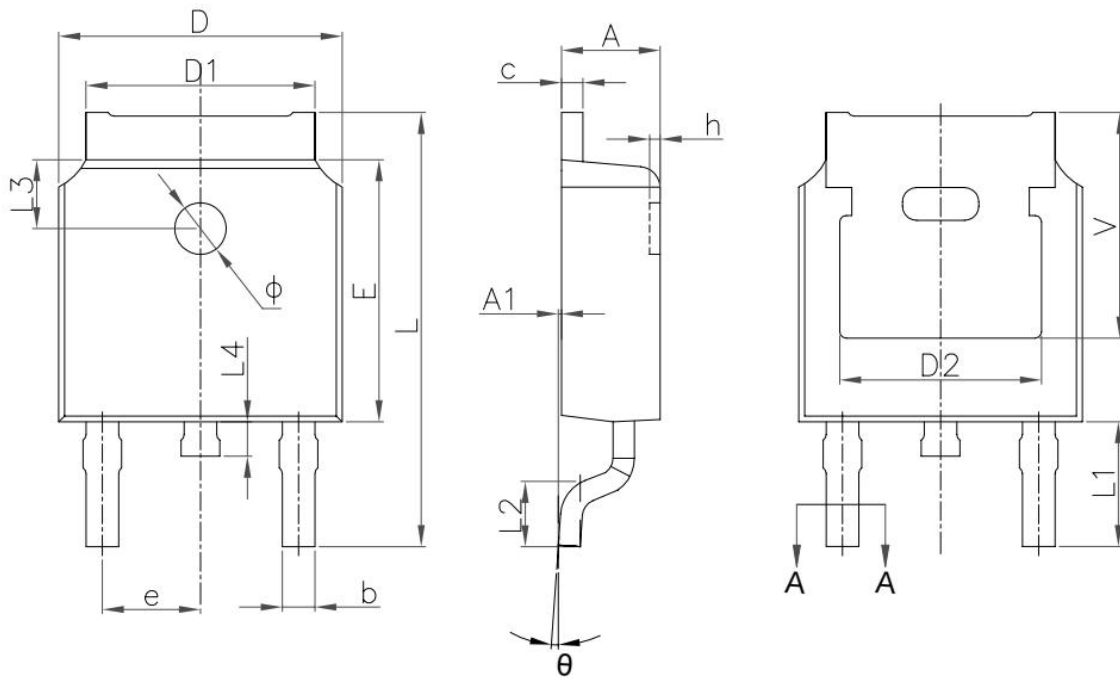
2) Switch Time Test Circuit:



3) Unclamped Inductive Switching Test Circuit & Waveforms



TO-252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.20	2.40	0.087	0.094
A1	0.00	0.13	0.000	0.005
b	0.66	0.86	0.026	0.033
b1	0.73	0.79	0.029	0.031
c	0.46	0.58	0.018	0.023
c1	0.50	0.52	0.020	0.020
D	6.50	6.70	0.256	0.264
D1	5.10	5.46	0.201	0.215
D2	4.83 REF		0.19REF	
E	6.00	6.20	0.236	0.244
e	2.19	2.39	0.086	0.094
L	9.80	10.40	0.386	0.409
L1	2.90 REF		0.11REF	
L2	1.40	1.70	0.055	
L3	1.60 REF		0.06REF	
L4	0.60	1.00	0.024	0.039
Φ	1.10	1.30	0.043	0.051
θ	0°	8°	0°	8°
h	0.00	0.30	0.000	0.012

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